TOSHIBA

MICROWAVE SEMICONDUCTOR

TECHNICAL DATA

POWER GaAs MMIC

S9750

PRELIMINARY

FEATURES :

- HIGH POWER
  Po = 28 dBm @ Pin = 8 dBm
- SUPER LOW DISTORTION
  P_{adj} = -65 dBc
  @Po = 27 dBm, 600 kHz offset
- HIGH GAIN
  Gp = 20 dB @ Pin = 8 dBm
- INPUT/OUTPUT PORT MATCHED TO 50 Ω
- HERMETICALLY SEALED PACKAGE

RF PERFORMANCE SPECIFICATIONS (Ta = 25°C)

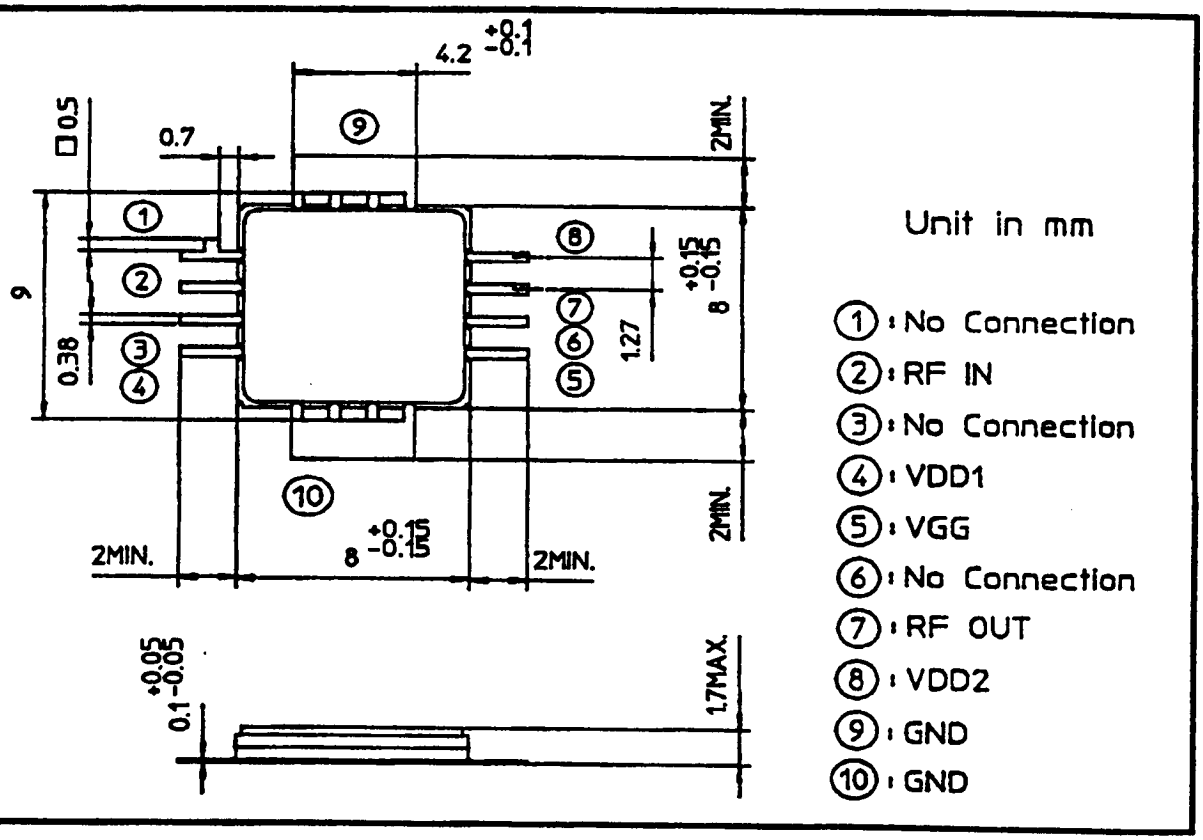
CHARACTERISTIC	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power	Po	V_{DD1} = V_{DD2} = 6V V_{GG}=-5V, f=1.9 GHz Pin = 8 dBm	dBm	27	28	-
Power Gain	Gp		dB	19	20	-
Drain Current	I_{DD}*		mA	-	360	500
Adjacent Channel Leakage Power	Padj	V_{DD1} = V_{DD2} = 6V V_{GG}=-5V, f=1.9 GHz Po = 27 dBm π/4-QPSK Modulation 600kHz Offset	dBc	-	-65	-

* I_{DD} = I_{DD1} + I_{DD2}

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	UNIT	RATING
Drain Supply Voltage	VDD1, VDD2	V	15
Gate Supply Voltage	VGG	V	-15
Input Power	Pin	dBm	13
Flange Temperature	Tf	°C	-30~+80
Storage Temperature	Tstg	°C	-65~+175

PACKAGE OUTLINE (2-8P1A)



HANDLING PRECAUTIONS FOR PACKAGED TYPE

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260 °C.